

PAUL SCHERRER INSTITUT



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Grayscale lithography in HSQ and the application of dose gradient shapes

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Blazed X-ray Diffraction Gratings

For application at Synchrotrons and XFELs
in the soft and tender x-ray range ($E \approx 40$
... 4000 eV)

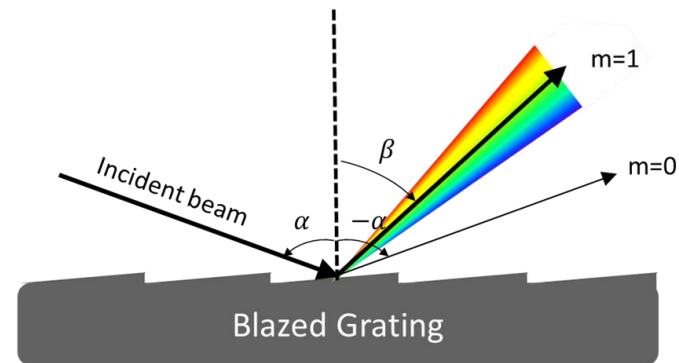
- Monochromators
- Analyzers for inelastic scattering (RIXS)
- Self-seeding & pulse compression

Blazed profile

Pitch: few microns down to 100 nm

Flat or curved substrates

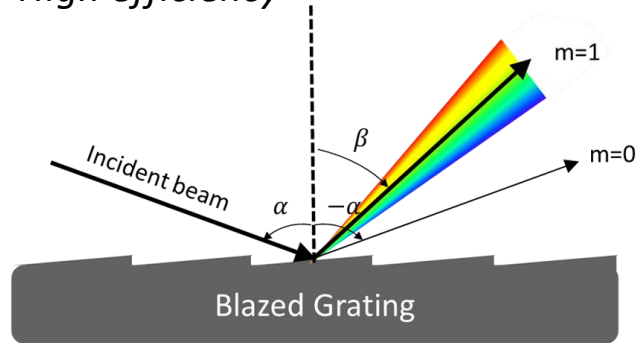
Up to 140 mm length



$$m\lambda = k_0 (\sin \alpha + \sin \beta)$$

Current fabrication methods

- *Ruling*
 - *Blazed gratings*
 - *High efficiency*



Sensitive to vibrations

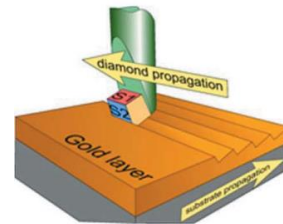
Quality of line patterns

Longer time for higher line density

Suppliers of high-quality gratings are very few

Availability of high quality gratings a key bottle-neck

Bigger problem in view of next generation light sources



Electron Beam Lithography - Gratings

High resolution in placement ($< 1 \text{ nm}$)

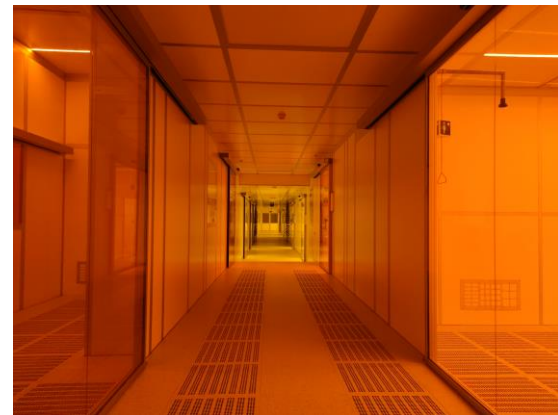
Sufficient throughput ($\sim 1 \text{ cm}^2/\text{hr}$)

Flat or curved substrates

Blazed or laminar structures

Length: up 140 mm

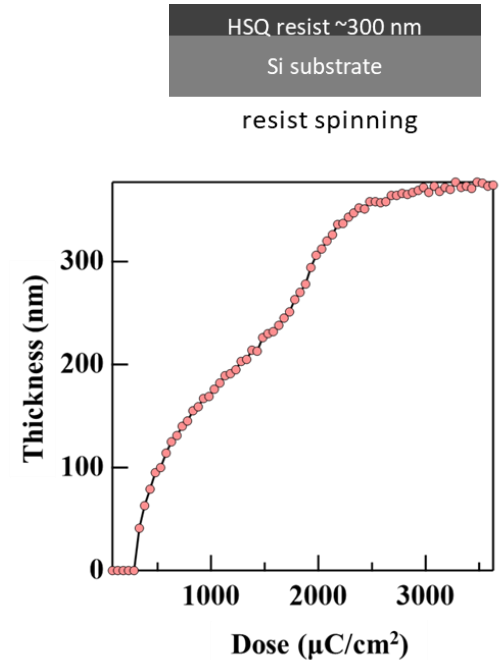
Pitch: few microns, down to few 100 nm



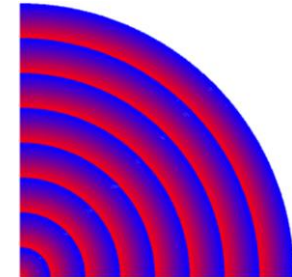
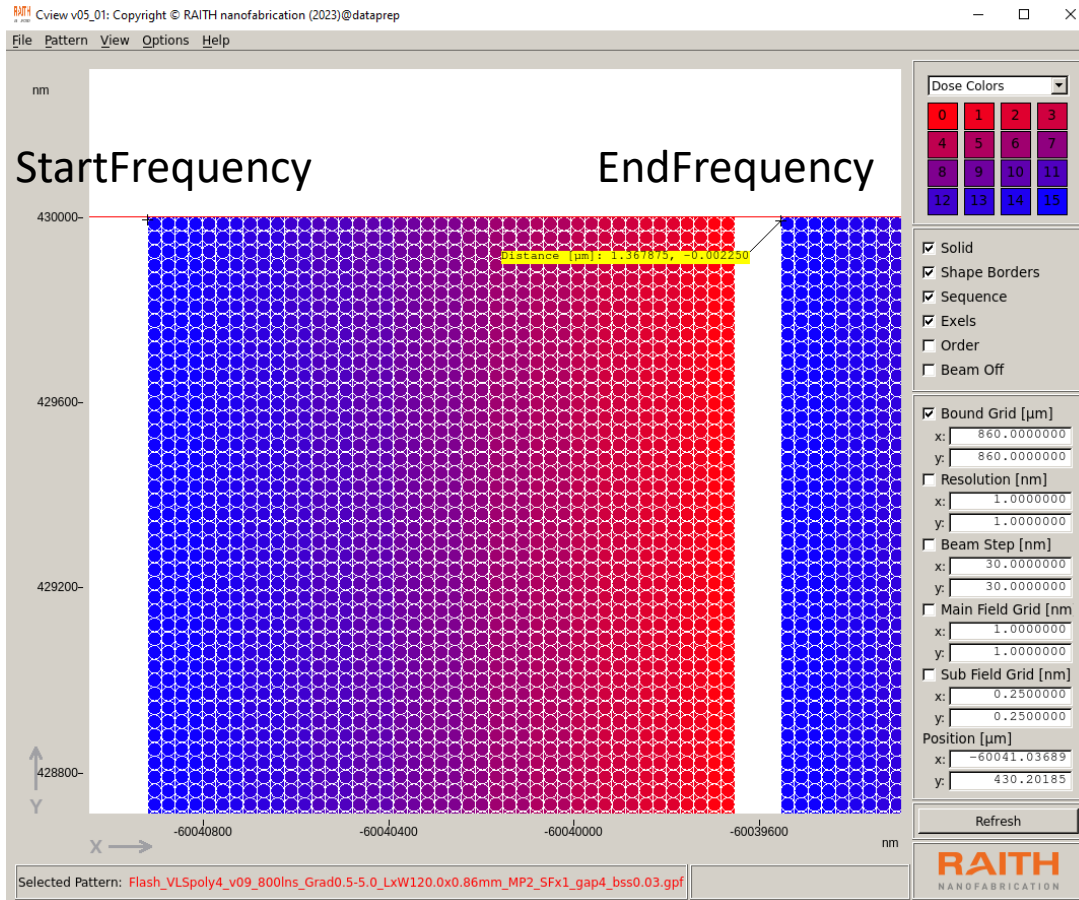
Several gratings with different pitch or blaze angle on the same substrate

Enhanced flexibility => more advanced optical designs such as curved lines

- Spin coating HSQ as resist (300 nm)
- Gray scale exposure
 - Dose gradient shapes (new development for EBPG)
- Convert resist structures into blazed grating lines
 - Mask oxidation (patent pending)



Dose gradient shape



Partial circle

Grayscale EBL and Thermal Oxidation of Silicon

Spin coating

- HSQ as resist, Thickness ~ 300 nm

Grey tone exposure

- Exposed area is converted to SiO_x

Development

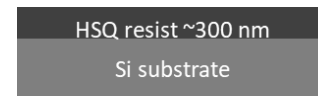
- NaOH based developer

Thermal oxidation

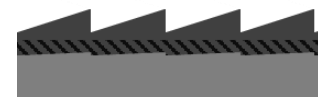
- Dry oxidation, Different SiO_x thickness => different oxidation speed

Oxide removal

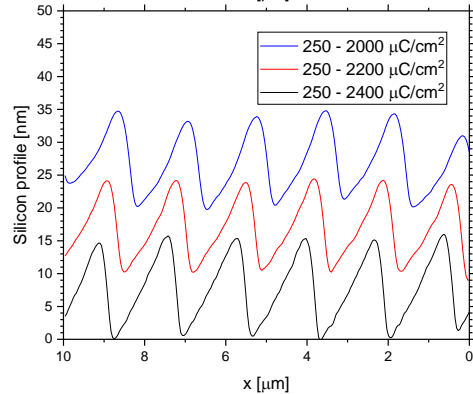
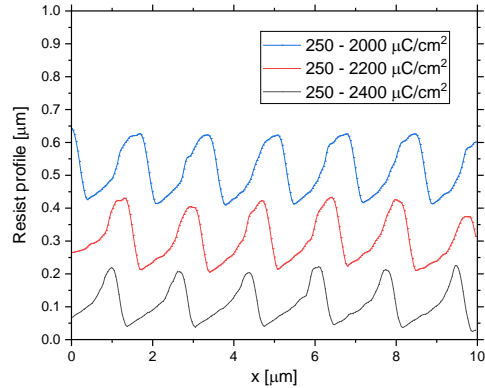
- Wet chemical oxide removal with HF => reduces the roughness



resist spinning



Grayscale EBL and Thermal Oxidation of Silicon



development



oxide removal

600l/mm (P1.666 μm)

Blazed angle = 1.61°

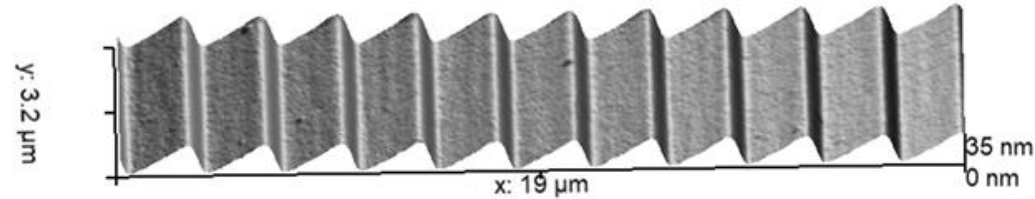
Step height = 31 nm

Anti-blazed angle = 4.88°

0.2 nm RMS roughness

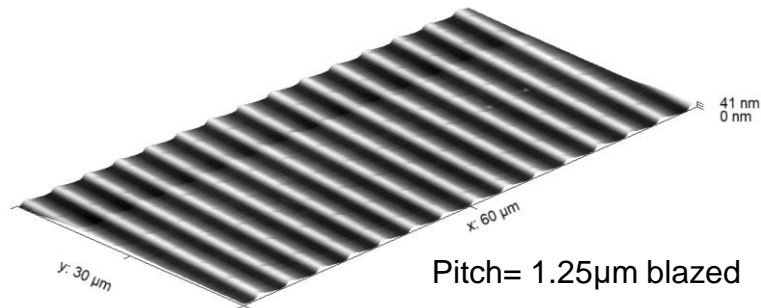
Dose: 275-2750 $\mu\text{C}/\text{cm}^2$

Beam step size 20 nm

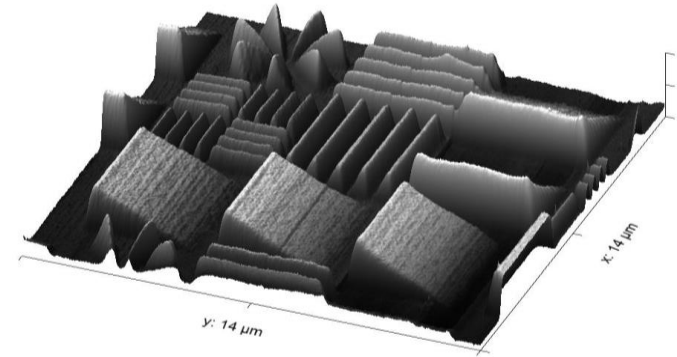


Pitch= 1.666 μm blazed

AFM image of blazed EBL test structures
250 l/mm – 2000 l/mm, 0.35 nm RMS roughness

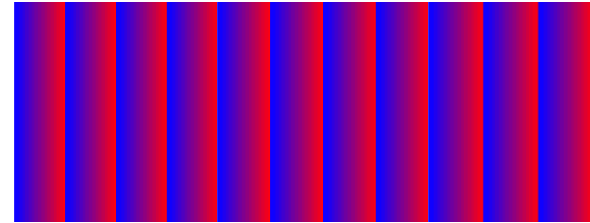


Pitch= 1.25 μm blazed

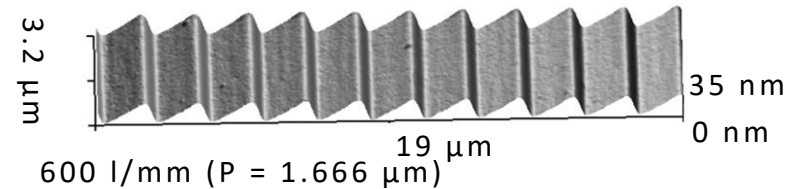


- From design
- To Grating
- To cool images (testing)

EBL design



AFM profile of test grating



600 l/mm ($P = 1.666 \mu\text{m}$)

Step height 31 nm

0.2 nm RMS roughness

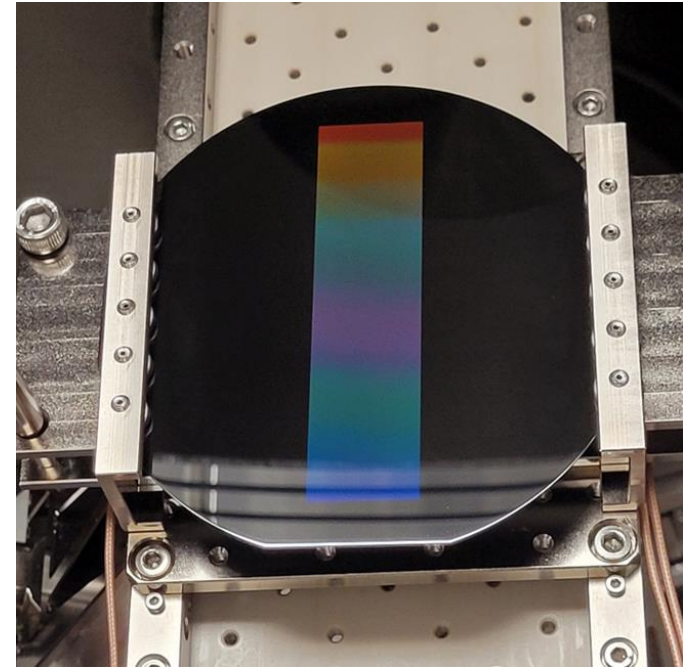
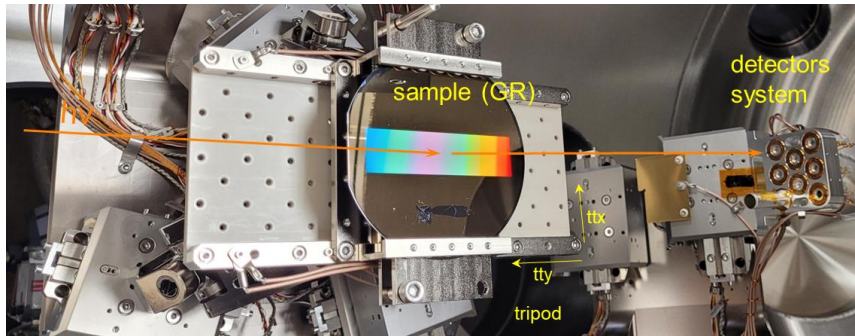
Dose: 275-2750 $\mu\text{C}/\text{cm}^2$

Beam step size 20 nm

Current 150 nA

At Wavelength Metrology @ BESSY II Optics Beamline on gold coated grating

Gold coated test grating in the reflectometer



Future steps

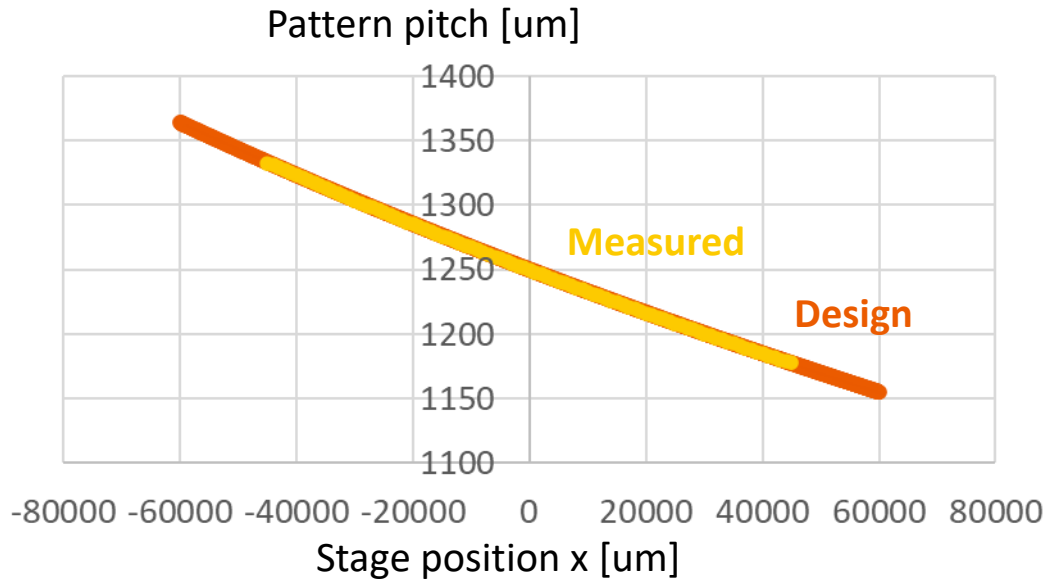
- Finalizing the lithography process
 - Full size gratings
 - Curved substrates
 - VLS gratings

Sneak peak – VLS gratings

Variable line spacing

- Line density = $a_0 + a_1x + a_2x^2 + a_3x^3$

Stage position x	-60000	um
Calculate line density	742.4984	lines/mm
Patternpitch	1346.804249	nm
Rounded pattern pitch	1347	nm
Scaling of MF in X	-14532	[ppm]
Scaled pitch corrected	-0.19574604	nm
Final pitch	1346.804254	nm
Final line density	742.4983973	lines/mm



Residual in pattern pitch
< 1 Angstrom

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Thank you!

Thank you for your
attention!

Question?

